

## 2SD2134

### Silicon NPN epitaxial planar type

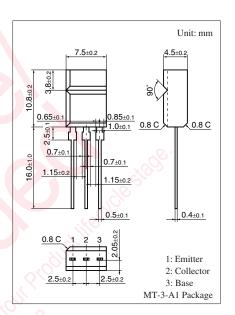
For low-frequency driver, high power amplification Complementary to 2SB1414

#### ■ Features

- Excellent collector current I<sub>C</sub> characteristics of forward current transfer ratio h<sub>FE</sub>
- High transition frequency f<sub>T</sub>
- A complementary pair with 2SB1414, is optimum for the driverstage of a 60 W to 100 W output amplifier.

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	150	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	150	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	V	
Collector current	$I_{C}$	1	A	
Peak collector current	I <sub>CP</sub>	1.5	A	
Collector power dissipation	P <sub>C</sub>	1.5	W	
Junction temperature	$T_{j}$	150	°°C	
Storage temperature	$T_{stg}$	-55 to +150	o °C	
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#### ■ Electrical Characteristics T<sub>a</sub> = 25°C ± 3°C

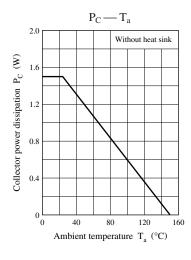
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 100 \ \mu A, I_B = 0$	150	55		V
Emitter-base voltage (Collector open)	$V_{\rm EBO}$	$I_E = 10 \mu\text{A},  I_C = 0$	5			V
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$	90		220	_
column	h <sub>FE2</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 500 \text{ mA}$	50			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.5	2.0	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.0	2.0	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		20		pF
(Common base, input open circuited)		160 Kg				

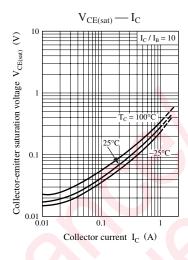
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

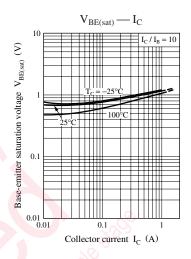
#### 2. \*: Rank classification

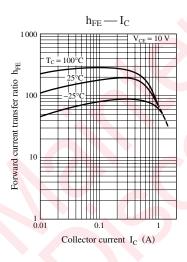
Rank	Q	R
$h_{\rm FE1}$	90 to 155	130 to 220

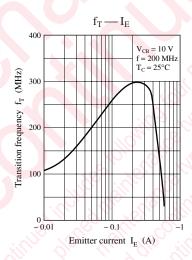
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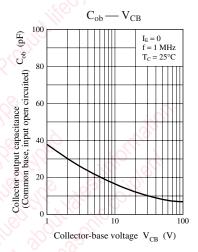


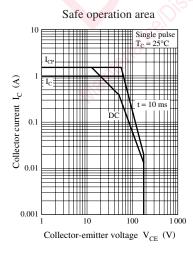


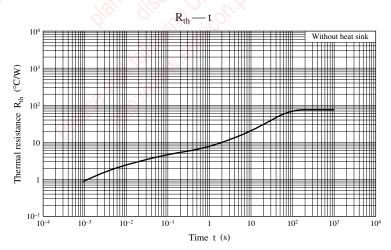












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